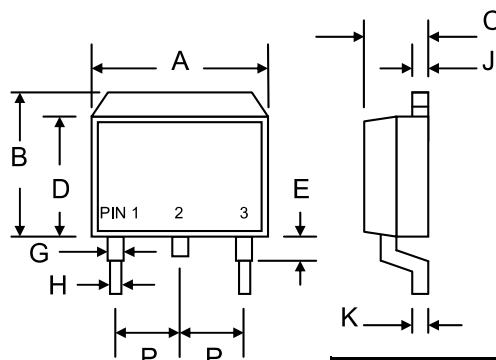


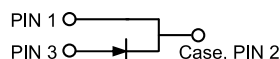
Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Super-Fast Recovery Time
- High Voltage Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in High Voltage, High Frequency Inverters, Free Wheeling, and Switching Power Supplies



Mechanical Data

- Case: D²PAK/TO-263, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Weight: 1.7 grams (approx.)
- Mounting Position: Any
- Marking: Device Code, See Page 3
- **Lead Free: For RoHS / Lead Free Version, Add “-LF” Suffix to Part Number, See Page 4**



D ² PAK/TO-263		
Dim	Min	Max
A	9.80	10.40
B	9.60	10.60
C	4.40	4.80
D	8.50	9.10
E	—	2.80
G	1.00	1.40
H	—	0.99
J	1.20	1.40
K	0.30	0.70
P	2.35	2.75
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MURHB820	MURHB830	MURHB840	MURHB860	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	300	400	600	V
RMS Reverse Voltage	V _{R(RMS)}	140	210	280	420	V
Average Rectified Output Current @T _C = 100°C	I _O	8.0				A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	125				A
Forward Voltage @I _F = 8.0A	V _{FM}	0.95	1.3	1.7		V
Peak Reverse Current @T _C = 25°C At Rated DC Blocking Voltage @T _C = 100°C	I _{RM}	10 500				μA
Reverse Recovery Time (Note 1)	t _{rr}	35	50			nS
Typical Junction Capacitance (Note 2)	C _J	85	50			pF
Thermal Resistance Junction to Ambient Thermal Resistance Junction to Case	R _{θJA} R _{θJC}	73 3.0				°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150				°C

Note: 1. Measured with I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A.
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

